

### Description

The PAM2306 is a dual step-down current-mode, DC-DC converter. At heavy load, the constant frequency PWM control provides excellent stability and transient response. To ensure the longest battery life in portable applications, the PAM2306 provides a powersaving Pulse-Skipping Modulation (PSM) mode to reduce quiescent current under light load operation.

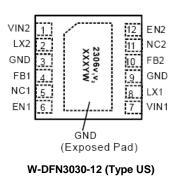
The PAM2306 supports a range of input voltages from 2.5V to 5.5V, allowing the use of a single Li+/Li-polymer cell, multiple Alkaline/NiMH cell, USB, and other standard power sources. The dual output voltages are available for 3.3V, 2.8V, 2.5V, 1.8V, 1.5V, 1.2V or adjustable. All versions employ internal power switch and synchronous rectifier to minimize external part count and realize high efficiency. During shutdown, the input is disconnected from the output and the shutdown current is less than 0.1A. Other key features include under-voltage lockout to prevent deep battery discharge.

### Features

- Efficiency up to 96%
- Only 40µA (Typ. Per Channel) Quiescent Current
- Output Current: Up to 1A per Channel
- Internal Synchronous Rectifier
- 1.5MHz Switching Frequency
- Soft Start
- Under-Voltage Lockout
- Short Circuit Protection
- Thermal Shutdown
- Small W-DFN3030-12 (Type US) Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/guality/product-definitions/</u>

### **Pin Assignments**

#### (Top View)



### Applications

- Cellular Phone
- Portable Electronics
- Personal Information Appliances
- Wireless and DSL Modems
- MP3 Players

- Notes:
  - 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
    - 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
    - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



PAM2306

# **Typical Applications Circuit**

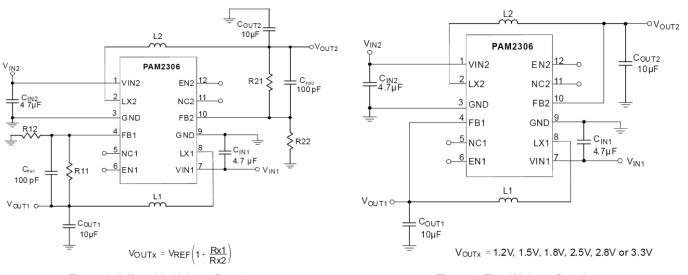


Figure 1. Adjustable Voltage Regulator

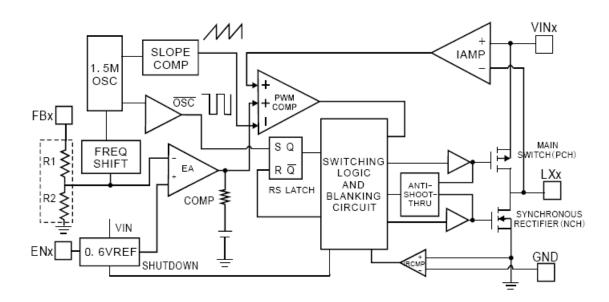
Figure 2. Fixed Voltage Regulator

# **Pin Descriptions**

Pin Number	Pin Name W-DFN3030-12 (Type US)	Function	
1	VIN2	Power Input of Channel 2.	
2	LX2	Pin for Switching of Channel 2.	
3, 9 Exposed Pad	GND	Ground. The exposed pad must be soldered to a large PCB and connected to GND for maximum power dissipation.	
4	FB1	Feedback of Channel 1.	
5, 11	NC1, NC2	No Connection.	
6	EN1	Chip Enable of Channel 1 (Active High). V <sub>EN1</sub> ≤ V <sub>IN1</sub> .	
7	VIN1	Power Input of Channel 1.	
8	LX1	Pin for Switching of Channel 1.	
10	FB2	Feedback of Channel 2.	
12	EN2	Chip Enable of Channel 2 (Active High). $V_{EN2} \leq V_{IN2}$ .	



# **Functional Block Diagram**



# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

These are stress ratings only and functional operation is not implied. Exposure to absolute maximum ratings for prolonged time periods may affect device reliability. All voltages are with respect to ground.

Parameter	Rating	Unit
Input Voltage	-0.3 to +6.5	V
EN1, FB1, LX1, EN2, FB2 and LX2 Pin Voltage	-0.3 to (V <sub>IN</sub> +0.3)	V
Maximum Junction Temperature	150	°C
Storage Temperature Range	-65 to +150	°C
Soldering Temperature	260, 10s	°C

# Recommended Operating Conditions (@TA = +25°C, unless otherwise specified.)

Parameter	Rating	Unit
Supply Voltage	2.5 to 5.5	V
Ambient Temperature Range	-40 to +85	°C
Junction Temperature Range	-40 to +125	°C

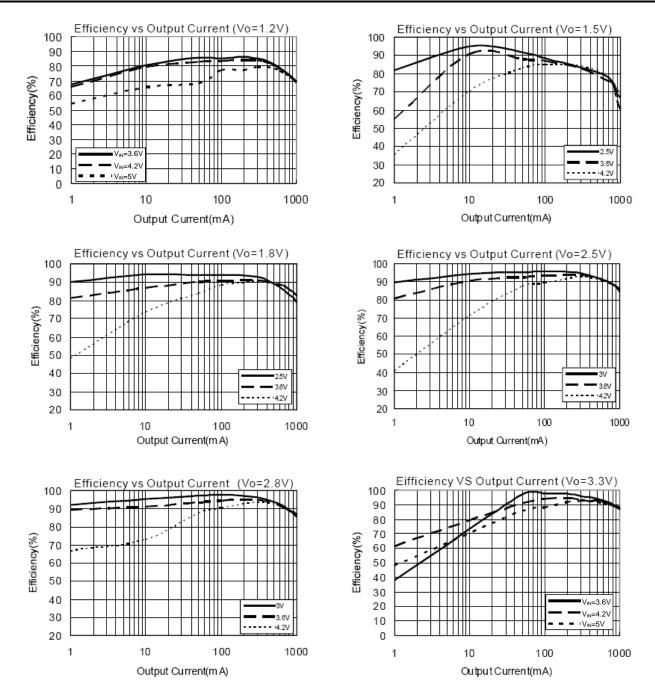
# **Thermal Information**

Parameter	Symbol	Package	Maximum	Unit
Thermal Resistance (Junction to Ambient)	θ <sub>JA</sub>	W-DFN3030-12 (Type US)	60	°C/W
Thermal Resistance (Junction to Case)	θ <sub>JC</sub>	W-DFN3030-12 (Type US)	8.5	°C/W
Power Dissipation	PD	W-DFN3030-12 (Type US)	1.66	W

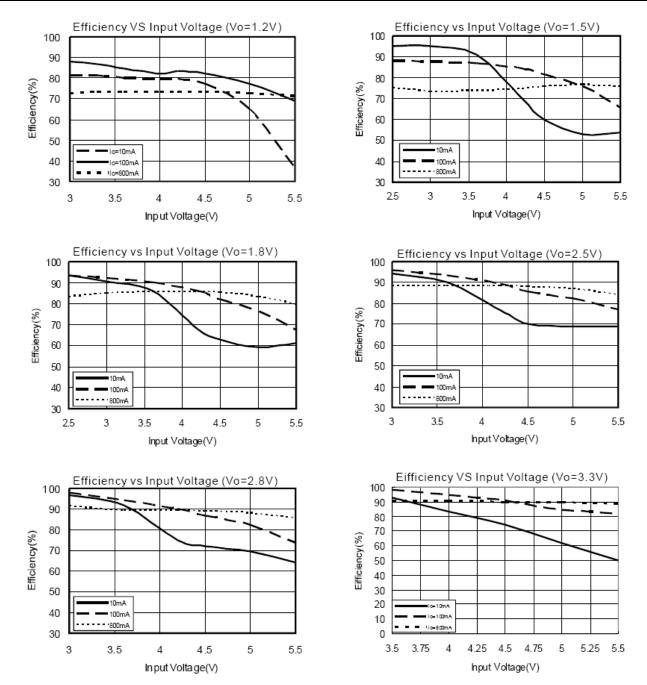


Parameter	Symbol	Test C	onditions	Min	Тур	Max	Unit
Input Voltage Range	Vin	—		2.5	_	5.5	V
Regulated Feedback Voltage	Vfb	—		0.588	0.6	0.612	V
Reference Voltage Line Regulation	ΔVfb	—		—	0.3	_	%/V
Regulated Output Voltage Accuracy	Vo	lo = 10mA		-3	_	+3	%
Peak Indictor Current	Ірк	VIN = 3V, VFB =	0.5V or Vo = 90%	—	1.5	_	А
Output Voltage Line Regulation	LNR	V <sub>IN</sub> = 2.5V to 5V	, lo = 10mA	—	0.2	0.5	%/V
Output Voltage Load Regulation	LDR	Io = 1mA to 1A		—	0.5	1.5	%
Quiescent Current (Per Channel)	lq	No load		—	40	70	μA
Shutdown Current (Per Channel)	I <sub>SD</sub>	$V_{EN} = 0V$		—	0.1	1	μA
On sillaton Francisco au		V <sub>O</sub> = 100%		1.2	1.5	1.8	MHz
Oscillator Frequency	TOSC	fosc VFB = 0V or Vo = 0V		—	500	_	kHz
Drain-Source On-State Resistance	Deckey	P MOSFET		—	0.3	0.45	Ω
Dialit-Source Off-State Resistance	RDS(ON)	I <sub>DS</sub> = 100mA	N MOSFET		0.35	0.5	Ω
SW Leakage Current (Per Channel)	ILSW	—			±0.01	1	μA
High Efficiency	η	—		_	96	_	%
EN Threshold High	VEH	—		1.5	_	_	V
EN Threshold Low	VEL	—		—	_	0.3	V
EN Leakage Current	IEN	—		—	±0.01	_	μA
Over Temperature Protection	OTP	—		—	+150		°C
OTP Hysteresis	OTH	—			+30	_	°C

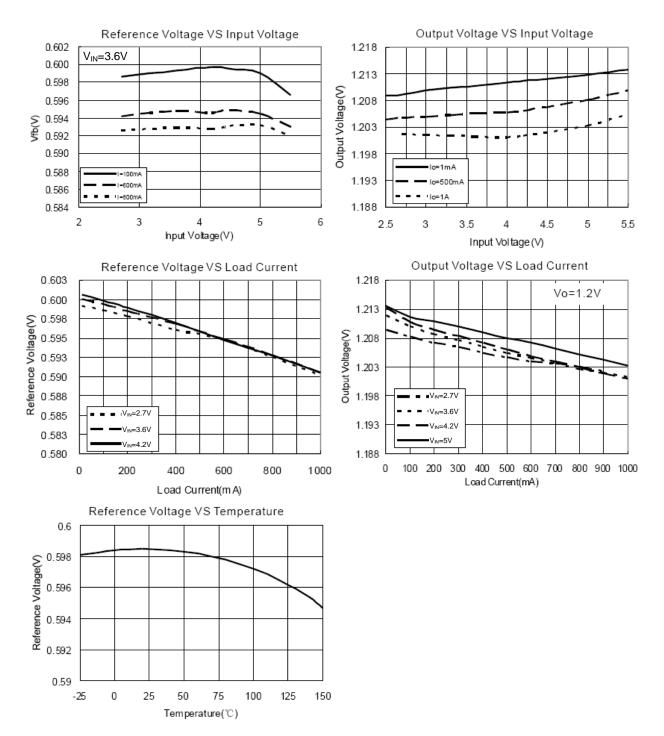




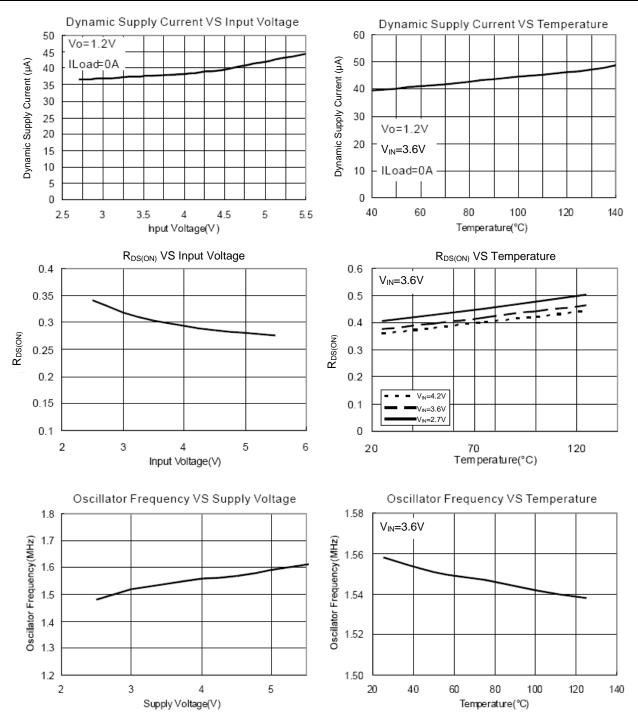




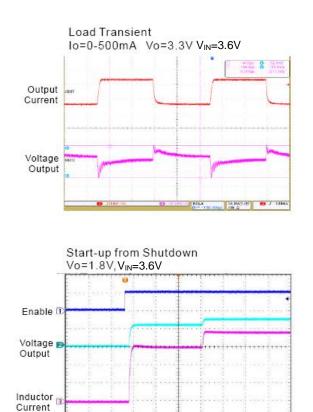










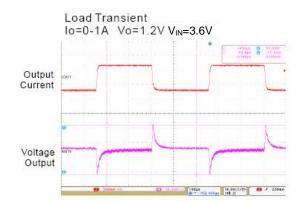


M 200µs A Ch1 J 1.36 V

11+\* 472.000µs

Ch1 2.00 V Ch3 200mA Q

311 1.00 V





# **Application Information**

The basic PAM2306 application circuit is shown in Page 2. External component selection is determined by the load requirement, selecting L first and then CIN and COUT.

#### Inductor Selection

For most applications, the value of the inductor will fall in the range of 1µH to 4.7µH. Its value is chosen based on the desired ripple current. Large value inductors lower ripple current and small value inductors result in higher ripple currents. Higher V<sub>IN</sub> or V<sub>OUT</sub> also increases the ripple current as shown in Equation 1. A reasonable starting point for setting ripple current is  $\Delta I_L = 400$ mA (40% of 1A).

$$\Delta I_{L} = \frac{1}{(f)(L)} V_{OUT} \left( 1 - \frac{V_{OUT}}{V_{IN}} \right)$$
 Equation (1)

The DC current rating of the inductor should be at least equal to the maximum load current plus half the ripple current to prevent core saturation. Thus, a 1.4A rated inductor should be enough for most applications (1A + 400mA). For better efficiency, choose a low DC-resistance inductor.

Vo	1.2V	1.5V	1.8V	2.5V	3.3V
L	2.2 µH	2.2 µH	2.2 µH	4.7 µH	4.7µH

#### CIN and COUT Selection

In continuous mode, the source current of the top MOSFET is a square wave of duty cycle VOUT/VIN. To prevent large voltage transients, a low ESR input capacitor sized for the maximum RMS current must be used. The maximum RMS capacitor current is given by:

$$C_{IN}$$
 required  $I_{RMS} \cong I_{OMAX} \frac{\left[V_{OUT} \left(V_{IN} - V_{OUT}\right)\right]^{1/2}}{V_{IN}}$ 

This formula has a maximum at  $V_{IN} = 2V_{OUT}$ , where  $I_{RMS} = I_{OUT}$  /2. This simple worst-case condition is commonly used for design because even significant deviations do not offer much relief. Note that the capacitor manufacturer's ripple current ratings are often based on 2000 hours of life. This makes it advisable to further derate the capacitor, or choose a capacitor rated at a higher temperature than required. Consult the manufacturer if there is any question.

The selection of COUT is driven by the required effective series resistance (ESR).

Typically, once the ESR requirement for  $C_{OUT}$  has been met, the RMS current rating generally far exceeds the I<sub>RIPPLE</sub> (P-P) requirement. The output ripple  $\Delta V_{OUT}$  is determined by:

$$\Delta V_{OUT} \cong \Delta I_{L} \left( \text{ESR} + \frac{1}{8 f C_{OUT}} \right)$$

Where f = operating frequency,  $C_{OUT}$  = output capacitance and  $\Delta I_L$  = ripple current in the inductor. For a fixed output voltage, the output ripple is highest at maximum input voltage since  $\Delta I_L$  increases with input voltage.

#### **Using Ceramic Input and Output Capacitors**

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. Using ceramic capacitors can achieve very low output ripple and small circuit size.

When choosing the input and output ceramic capacitors, choose the X5R or X7R dielectric formulations. These dielectrics have the best temperature and voltage characteristics of all the ceramics for a given value and size.

#### **Thermal Consideration**

Thermal protection limits power dissipation in the PAM2306. When the junction temperature exceeds +150°C, the OTP (Over Temperature Protection) starts the thermal shutdown and turns the pass transistor off. The pass transistor resumes operation after the junction temperature drops below +120°C.

For continuous operation, the junction temperature should maintain below +125°C.

The power dissipation is defined as:

$$P_{D} = I_{O}^{2} \frac{V_{O}R_{DS(ON)H} + (V_{IN} - V_{O})R_{DS(ON)L}}{V_{IN}} + (t_{SW}F_{S}I_{O} + I_{Q})V_{IN}$$

IQ is the step-down converter quiescent current. The term tsw is used to estimate the full load step-down converter switching losses.



### Application Information (continued)

#### Thermal Consideration (continued)

For the condition where the step-down converter is in dropout at 100% duty cycle, the total device dissipation reduces to:

$$P_{\rm D} = I_{\rm O}^2 R_{\rm DS(ON)H} + I_{\rm Q} V_{\rm IN}$$

Since RDS(ON), quiescent current, and switching losses all vary with input voltage, the total losses should be investigated over the complete input voltage range. The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surrounding airflow and temperature difference between junction and ambient. The maximum power dissipation can be calculated by the following formula:

$$P_{D} = \frac{T_{J(MAX)} - T_{A}}{\theta_{JA}}$$

Where  $T_{J(MAX)}$  is the maximum allowable junction temperature +125°C. T<sub>A</sub> is the ambient temperature and  $\theta_{JA}$  is the thermal resistance from the junction to the ambient. Based on the standard JEDEC for a two layers thermal test board, the thermal resistance  $\theta_{JA}$  of WDFN3X3 is 60°C/W. The maximum power dissipation at  $T_A = +25^{\circ}$ C can be calculated by following formula:

 $P_D = (125^{\circ}C - 25^{\circ}C)/60^{\circ}C/W = 1.66W$ 

#### Setting the Output Voltage

The internal reference is 0.6V (Typical). The output voltage is calculated as below:

$$V_O = 0.6 \times \left(1 + \frac{R1}{R2}\right)$$

The output voltage is given by Table 1.

Vo	R1	R2
1.2V	100k	100k
1.5V	150k	100k
1.8V	200k	100k
2.5V	380k	120k
3.3V	540k	120k

Table 1: Resistor Selection for Output Voltage Setting

#### 100% Duty Cycle Operation

As the input voltage approaches the output voltage, the converter turns the P-Channel transistor continuously on. In this mode the output voltage is equal to the input voltage minus the voltage drop across the P-Channel transistor:

VOUT = VIN - ILOAD (RDS(ON) + RL)

Where RDS(ON) = P-Channel switch ON Resistance, ILOAD = Output Current, RL = Inductor DC Resistance.

#### UVLO and Soft-Start

The reference and the circuit remain reset until the V<sub>IN</sub> crosses its UVLO threshold.

The PAM2306 has an internal soft-start circuit that limits the in-rush current during start-up. This prevents possible voltage drops of the input voltage and eliminates the output voltage overshoot. The soft-start acts as a digital circuit to increase the switch current in several steps to the P-Channel current limit (1500mA).

#### **Short Circuit Protection**

The switch peak current is limited cycle-by-cycle to a typical value of 1500mA. In the event of an output voltage short circuit, the device operates with a frequency of 400kHz and minimum duty cycle, therefore the average input current is typically 200mA.

#### **Thermal Shutdown**

When the die temperature exceeds +150°C, a reset occurs and the reset remains until the temperature decrease to +120°C, at which time the circuit can be restarted.



# Application Information (continued)

#### PCB Layout Check List

When laying out the printed circuit board, the following checklist should be used to ensure proper operation of the PAM2306. These items are also illustrated graphically in Figure 3. Check the following in your layout:

- 1. The power traces, consisting of the GND trace, the SW trace and the VIN trace should be kept short, direct and wide.
- 2. Does the FB pin connect directly to the feedback resistors? The resistive divider R1/R2 must be connected between the (+) plate of Court and ground.
- 3. Does the (+) plate of CIN connect to VIN as closely as possible? This capacitor provides the AC current to the internal power MOSFETs.
- 4. Keep the switching node, SW, away from the sensitive FB node.
- 5. Keep the (–) plates of C<sub>IN</sub> and C<sub>OUT</sub> as close as possible.

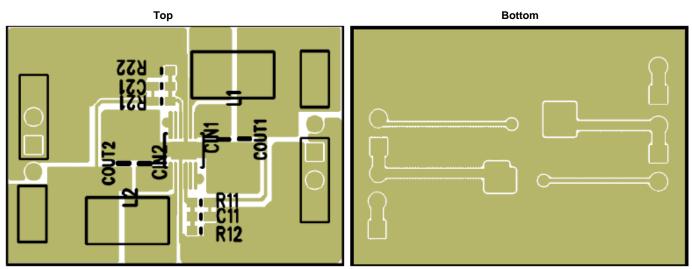


Figure 3. PAM2306 Suggested Layout



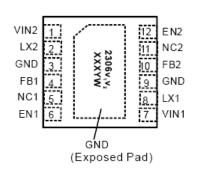
# **Ordering Information**

	PAM230	6 <u>X X X V</u> 1 V2		
Pin Configu A: Type 1. VIN2 2. LX2 3. GND 4. FB1 5. NC1 6. EN1 7. VIN1	ype Numbe 30-12 P: 12		K: 3.3V   H: 2.8V   G: 2.5V   E: 1.8V   C: 1.5V	/oltage V <sub>2</sub>
8. LX1 9. GND 10. FB2 11. NC2 12. EN2				

Part Number	Marking	Package Type	Packaging
PAM2306AYPV1V2 (Note 4)	2306v1v2 XXXYW	W-DFN3030-12 (Type US)	3000 Units/ Tape & Reel

Note: 4. PAM2306AYPKE is Active. All other versions are NRND or EOL. For recommended alternatives to NRND/EOL devices, <u>Contact Us</u>.

# Marking Information



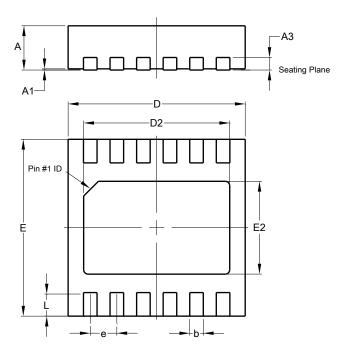
(Top View)

- v1: Output Voltage 1
- v2: Output Voltage 2
- (refer to "Ordering Information")
- X: Internal Code
- Y: Year W: Week



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.



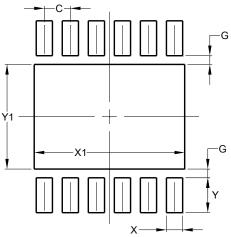
V	W-DFN3030-12 (Type US)					
Dim	Dim Min Max Typ					
Α	0.70	0.80				
A1	0	0.05				
A3	0.175	0.250				
b	0.150	0.250				
D	2.950	3.050				
D2	2.30	2.65				
е	-	-	0.45			
E	2.950	3.050				
E2	1.40	1.75				
L	0.35	0.45				
	imens	ions in	mm			

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### W-DFN3030-12 (Type US)

W-DFN3030-12 (Type US)



Dimensions	Value (in mm)
С	0.45
G	0.15
Х	0.28
X1	2.60
Y	0.60
Y1	1.80



#### IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2020, Diodes Incorporated

#### www.diodes.com